

N-channel 30 V 1.5 mΩ logic level MOSFET in D2PAK

12 October 2012

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low Rdson for low conduction losses

1.3 Applications

- Electronic fuse
- Hot swap
- Load switch
- Soft start

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|---------------------|----------------------------------|---|-----|-----|------|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 30 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | - | 120 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 401 | W |
| Static chara | acteristics | 1 | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | | - | 1.3 | 1.5 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | | - | 1.7 | 1.85 | mΩ |
| Dynamic ch | naracteristics | 1 | | | | | |
| Q _{GD} | gate-drain charge | V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 14; Fig. 15 | | - | 33.2 | - | nC |
| Q _{G(tot)} | total gate charge | V _{GS} = 10 V; I _D = 25 A; V _{DS} = 15 V; Fig. 14; Fig. 15 | | - | 228 | - | nC |



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| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|----------------------|---|--|--|-----|-----|------|------|
| Avalanche rug | Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 120 \text{ A};$ $V_{sup} \leq 30 \text{ V}; \text{ unclamped}; \text{R}_{\text{GS}} = 50 \Omega;$ $\overline{\text{Fig. 3}}$ | | - | - | 1990 | mJ |

[1] Capped at 120A due to package

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain[1] | | |
| 3 | S | source | | G UF A |
| mb | D | mounting base; connected to drain | D2PAK (SOT404) | mbb076 S |

[1] It is not possible to make connection to pin 2.

3. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|---------|--|---------|--|--|--|--|
| Type number | Package | | | | | | |
| | Name | Description | Version | | | | |
| PSMN1R5-30BLE | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | | | |

4. Marking

| Table 4. Marking codes | |
|--------------------------|---------------|
| Type number | Marking code |
| PSMN1R5-30BLE | PSMN1R5-30BLE |

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--|----------------------|--|-----|-----------------|--------------------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 30 | V |
| V _{DGR} | drain-gate voltage | $T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 30 | V |
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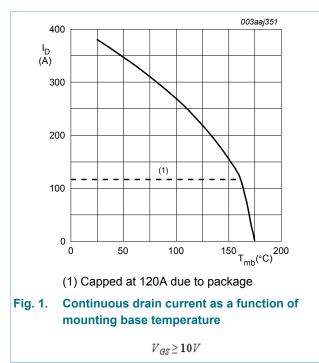
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|------|
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u> | [1] | - | 120 | А |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | 120 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4 | | - | 1521 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 401 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-dra | in diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 120 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$ | | - | 1521 | А |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 120 \; A; \\ V_{sup} \leq 30 \; V; \; unclamped; \; R_{GS} = 50 \; \Omega; \\ \hline Fig. 3 \end{array}$ | | - | 1990 | mJ |

[1] Capped at 120A due to package



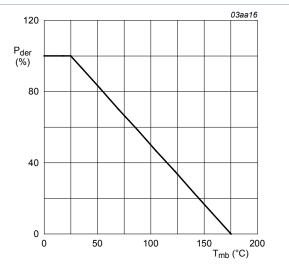


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

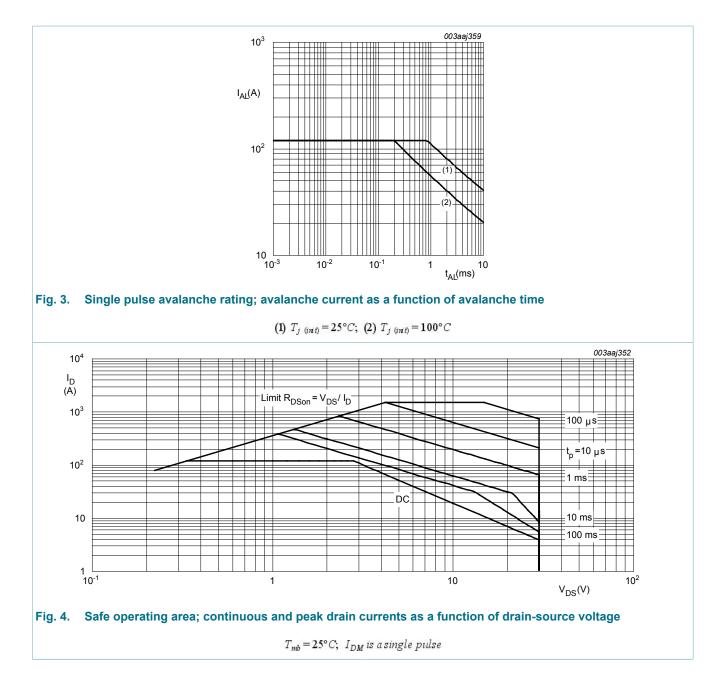
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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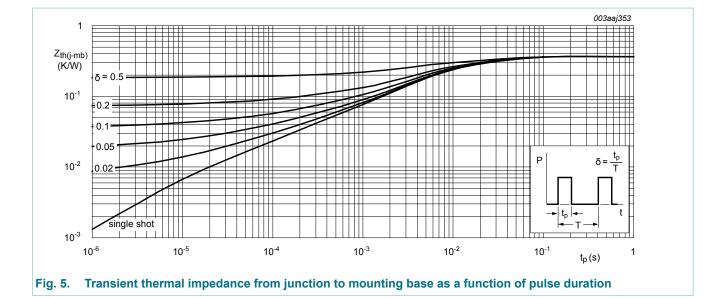
6. Thermal characteristics

| Table 6. The | rmal characteristics | | | | | |
|-----------------------|---|------------------------------|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. <u>5</u> | - | 0.3 | 0.37 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint; FR4 board | - | 50 | - | K/W |

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7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|----------------------------------|--|-----|-----|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 27 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 30 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10 | 0.5 | - | - | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 11; Fig. 10 | 1.3 | 1.7 | 2.15 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10 | - | - | 2.45 | V |
| I _{DSS} | drain leakage current | V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.5 | 10 | μA |
| | | V_{DS} = 30 V; V_{GS} = 0 V; T_j = 100 °C | - | - | 200 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | 100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | - | 1.3 | 1.5 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 12; Fig. 13 | - | - | 2.1 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12 | - | 1.7 | 1.85 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 13 | - | - | 2.9 | mΩ |

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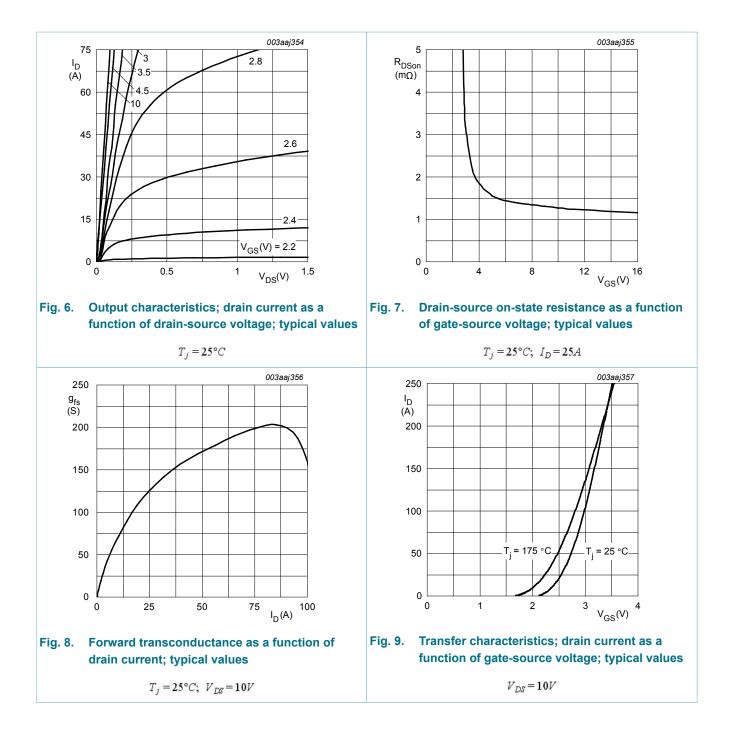
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------------|---|-----|-------|-----|------|
| R _G | internal gate resistance (AC) | f = 1 MHz | 0.5 | 1.1 | 2.2 | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14; Fig. 15 | - | 228 | - | nC |
| | | I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14; Fig. 15 | - | 108 | - | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 210 | - | nC |
| Q _{GS} | gate-source charge | I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V; | - | 31.8 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | Fig. 14; Fig. 15 | - | 21.5 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate- source charge | | - | 10.3 | - | nC |
| Q _{GD} | gate-drain charge | | - | 33.2 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 25 A; V _{DS} = 15 V; <u>Fig. 14</u> ; <u>Fig. 15</u> | - | 2.5 | - | V |
| C _{iss} | input capacitance | V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; | - | 14934 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 16</u> | - | 2741 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 1168 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; R _L = 0.6 Ω; V _{GS} = 4.5 V; | - | 100.6 | - | ns |
| tr | rise time | R _{G(ext)} = 4.7 Ω; T _j = 25 °C | - | 156.1 | - | ns |
| t _{d(off)} | turn-off delay time | 1 | - | 191.8 | - | ns |
| t _f | fall time | 1 | - | 99.2 | - | ns |
| Source-drai | n diode | | I | | | |
| V _{SD} | source-drain voltage | I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u> | - | 0.78 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 25 A; dI _S /dt = 100 A/µs; V _{GS} = 0 V; | - | 62.5 | - | ns |
| Q _r | recovered charge | V _{DS} = 15 V | - | 96.8 | - | nC |

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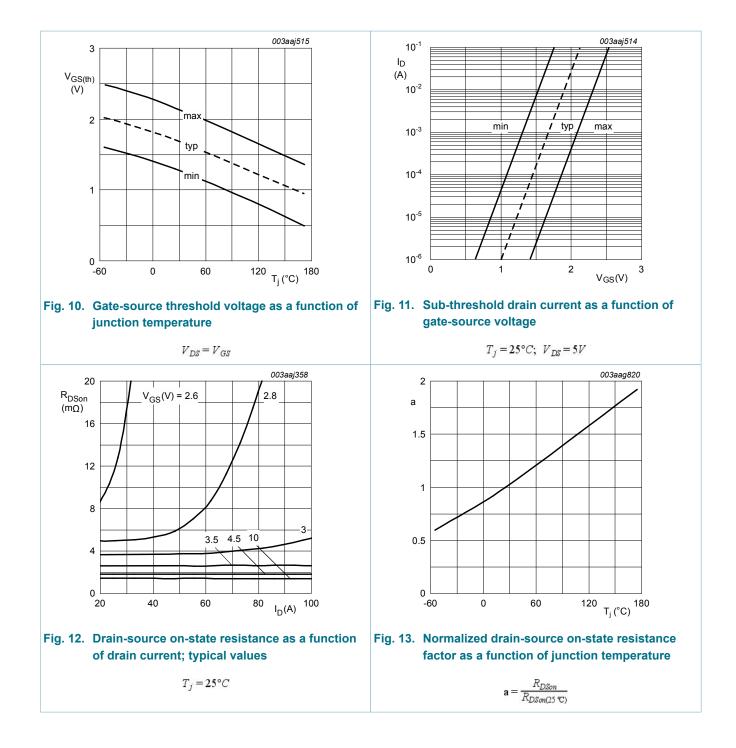
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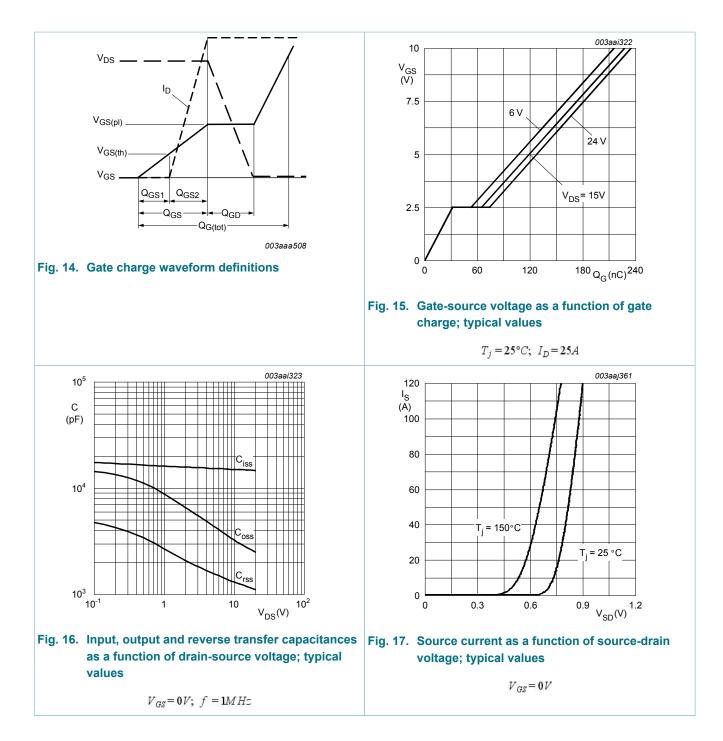


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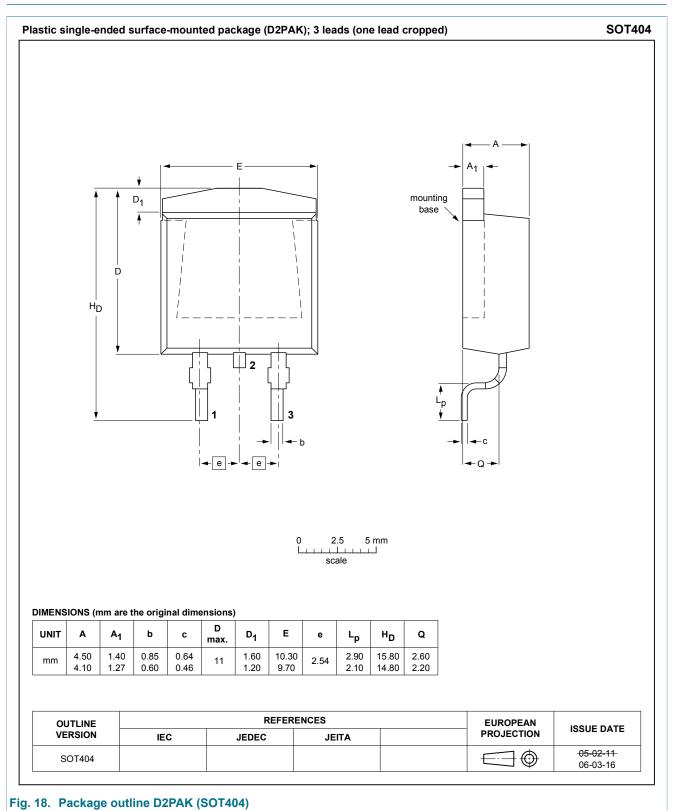


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8. Package outline



N-channel 30 V 1.5 mΩ logic level MOSFET in D2PAK

9. Legal information

9.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
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